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Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY						
V _{DS} (V)	30					
$R_{DS(on)}$ (Ω) at $V_{GS} = 10 \text{ V}$	0.00135					
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.00175					
I _D (A)	120					
Configuration	Single					
Package	TO-263					

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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N-Channel MOSFET) S

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage	V_{DS}	30	V			
Gate-source voltage	V_{GS}	± 20				
Continuous drain current ^a	T _C = 25 °C	- I _D	120			
Continuous drain current -	T _C = 125 °C		120			
Continuous source current (diode conduction) a	I _S	120	Α			
Pulsed drain current ^b	I _{DM}	360				
Single pulse avalanche current	L = 0.1 mH	I _{AS}	72			
Single pulse avalanche energy	L = 0.1 IIII1	E _{AS}	259	mJ		
Maximum power dissipation ^b	T _C = 25 °C	Pn	375	W		
waximum power dissipation	T _C = 125 °C	r'D	125	VV		
Operating junction and storage temperature range		T_J,T_stg	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient F	PCB mount c	R_{thJA}	40	°C/W		
Junction-to-case (drain)		R_{thJC}	0.4	C/VV		

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	\ \ \	
Gate-source leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 30 V	-	-	1		
Zero gate voltage drain current		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	800	μA	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	100	-	-	Α	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 40 A	-	0.00110	0.00135	Ω	
		V _{GS} = 10 V	I _D = 40 A, T _J = 125 °C	-	-	0.00191		
		V _{GS} = 10 V	I _D = 40 A, T _J = 175 °C	-	-	0.00220		
		V _{GS} = 4.5 V	I _D = 35 A	-	0.00143	0.00175	Ω	
Forward transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 40 A	-	233	-	S	
Dynamic ^b		•				l .		
Input capacitance	C _{iss}		V _{DS} = 15 V, f = 1 MHz	-	20 090	28 000	pF	
Output capacitance	C _{oss}	V _{GS} = 0 V		-	7000	9500		
Reverse transfer capacitance	C _{rss}			-	540	750		
Total gate charge ^c	Qq		V _{GS} = 10 V V _{DS} = 15 V, I _D = 50 A		295	450	nC	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V			59	-		
Gate-drain charge ^c	Q _{gd}				59	-		
Gate resistance	Rq	f = 1 MHz		0.5	1.11	1.7	Ω	
Turn-on delay time c	t _{d(on)}	$V_{DD} = 15 \text{ V}, R_1 = 0.2 \Omega$		-	30	45		
Rise time ^c	t _r			-	240	360		
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 50 A$,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	98	150	ns	
Fall time ^c	t _f			-	44	70	İ	
Source-Drain Diode Ratings and Chara	cteristics ^b	•			<u> </u>	l .		
Pulsed current ^a	I _{SM}			-	-	360	Α	
Forward voltage	V _{SD}	I _F = 60 A, V _{GS} = 0 V		-	0.8	1.5	V	
Body diode reverse recovery time	t _{rr}	I _F = 35 A, di/dt = 100 A/μs		-	96	195	ns	
Body diode reverse recovery charge	Q _{rr}			-	185	370	nC	
Reverse recovery fall time	t _a			-	48	-		
Reverse recovery rise time	t _b	1		-	48	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-3.4	-	Α	

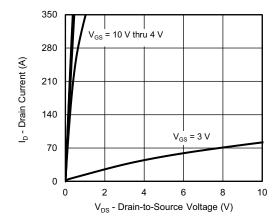
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

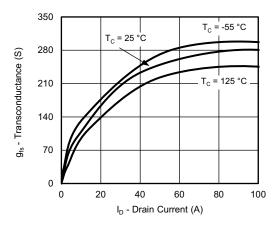
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



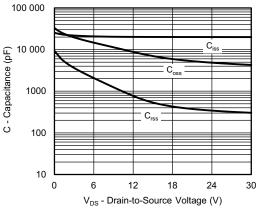
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



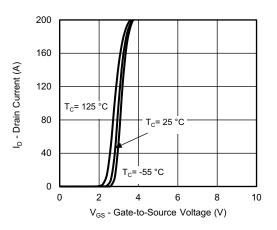
Output Characteristics



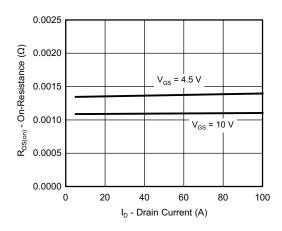
Transconductance



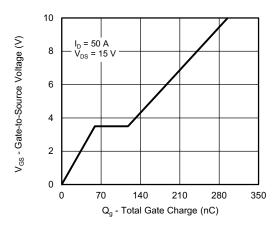
Capacitance



Transfer Characteristics



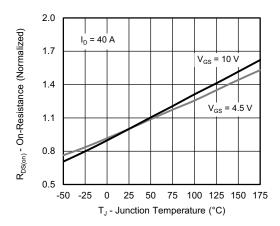
On-Resistance vs. Drain Current



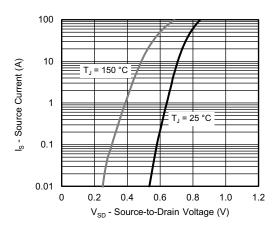
Gate Charge



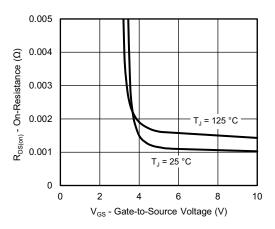
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



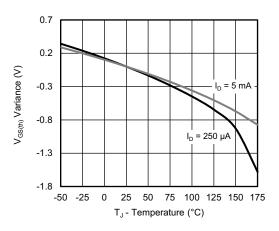
On-Resistance vs. Junction Temperature



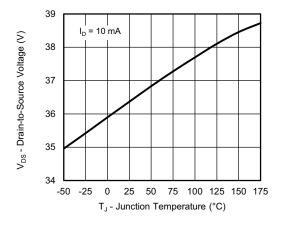
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



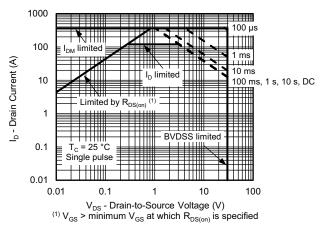
Threshold Voltage



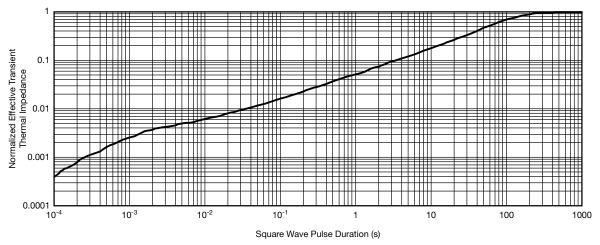
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



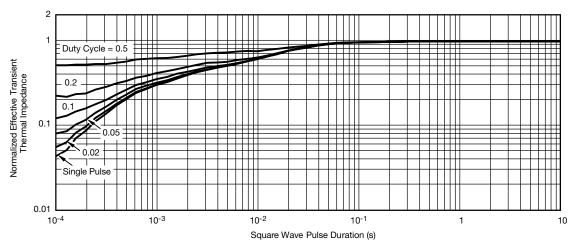
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

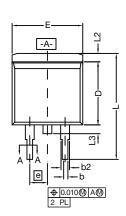
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

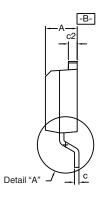
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

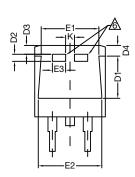
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg276633.



TO-263 (D²PAK): 3-LEAD

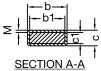








DETAIL A (ROTATED 90°)



_ - b1 	
≥ 	- -

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INC	HES	MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
C	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1 0.22		0.240	5.588	6.096	
D2		0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
D4		0.044	0.052	1.118	1.321	
E		0.380	0.410	9.652	10.414	
	E1	0.245	-	6.223	=	
	E2	0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
е		0.100) BSC	2.54 BSC		
K		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
	L2	0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010) BSC	0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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